BYV72F series

GENERAL DESCRIPTION

Glass passivated, high efficiency, dual, rectifier diodes in a full pack, plastic envelope, featuring low forward voltage drop, ultra-fast recovery times and soft recovery characteristic. They are intended for use in switched mode power supplies and high frequency circuits in general where low conduction and switching losses are essential.

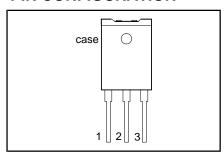
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BYV72F-	100	150	200	
V_{RRM}	Repetitive peak reverse voltage	100	150	200	V
V_{F}	Forward voltage	0.90	0.90	0.90	V
I _{O(AV)}	Output current (both diodes conducting)	20	20	20	Α
t _{rr}	Reverse recovery time	28	28	28	ns

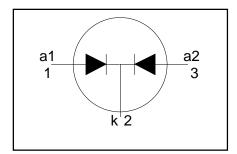
PINNING - SOT199

PIN	DESCRIPTION
1	anode 1 (a)
2	cathode (k)
3	anode 2 (a)

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V _{RRM} V _{RWM} V _R	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage			-100 100 100 100	-150 150 150 150	-200 200 200 200	>>>
I _{O(AV)}	Output current (both diodes conducting) ²	square wave; δ = 0.5; $T_{hs} \le 78$ °C sinusoidal; a = 1.57; $T_{hs} \le 78$ °C	-		20 20		A A
I _{O(RMS)} I _{FRM}	RMS forward current Repetitive peak forward current per diode	$t = 25 \mu s; δ = 0.5;$ $T_{hs} \le 78 °C$	- -		20 30		A A
I _{FSM}	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; with reapplied	-		150 160		A A
I ² t T _{stg} T _j	I ² t for fusing Storage temperature Operating junction temperature	$V_{RWM(max)}$ t = 10 ms	- -40 -		112 150 150		A ² s °C °C

¹ $T_{hs} \le 125$ °C for thermal stability.

² Neglecting switching and reverse current losses.

Philips Semiconductors Product specification

Rectifier diodes ultrafast

BYV72F series

ISOLATION LIMITING VALUE & CHARACTERISTIC

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. ≤ 65 % ; clean and dustfree	ı		2500	>
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	22	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-hs}$	Thermal resistance junction to heatsink Thermal resistance junction to ambient	both diodes conducting with heatsink compound without heatsink compound per diode with heatsink compound without heatsink compound in free air		- - - - 35	4.0 8.0 5.0 9.0	K/W K/W K/W K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

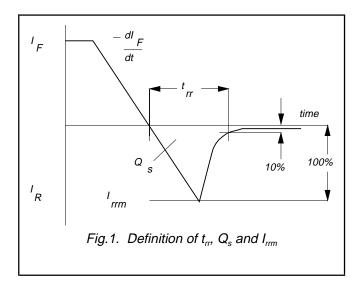
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage (per diode)	$I_F = 15 \text{ A}; T_i = 150^{\circ}\text{C}$	-	0.83	0.90	V
		I _F = 15 A	-	0.95	1.05	V
		$I_{\rm F} = 30 \text{ A}$	-	1.00	1.20	V
l _R	Reverse current (per diode)	$\dot{V}_R = V_{RWM}$; $T_i = 100 ^{\circ}C$	-	0.5	1	mΑ
"	l "	$V_R = V_{RWM}$	-	10	100	μΑ

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Q_s	Reverse recovery charge (per diode)	$I_F = 2 \text{ A}; V_R \ge 30 \text{ V}; -dI_F/dt = 20 \text{ A}/\mu\text{s}$	-	6	15	nC
t _{rr}		$I_F = 1 \text{ A; } V_R \ge 30 \text{ V;} \\ -dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	20	28	ns
I _{rrm}	/	$I_F = 10 \text{ A}; V_R \ge 30 \text{ V};$ $-dI_F/dt = 50 \text{ A}/\mu\text{s}; T_i = 100 ^{\circ}\text{C}$	-	2	2.4	Α
V_{fr}		$I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A/}\mu\text{s}$	-	1	-	V

BYV72F series



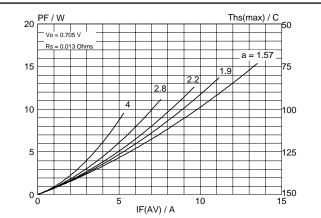
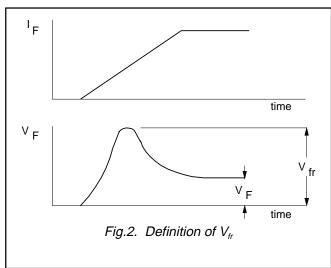
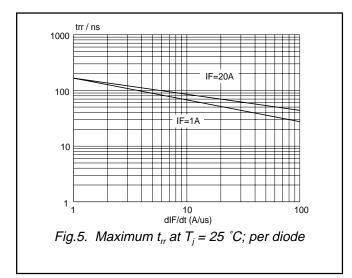


Fig.4. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = form factor $= I_{F(RMS)} / I_{F(AV)}$.





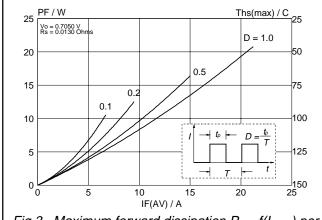
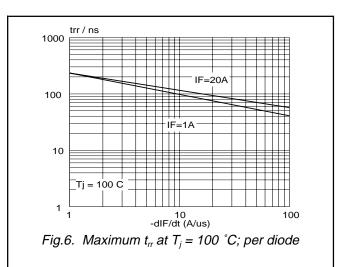
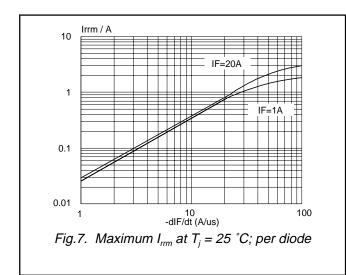
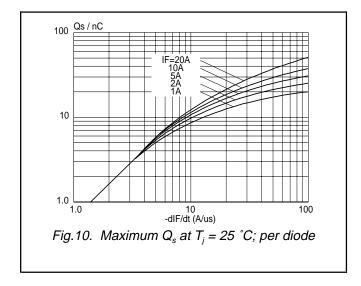


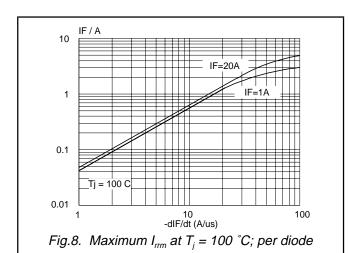
Fig.3. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

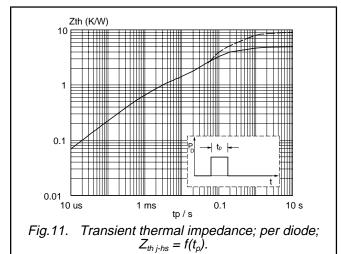


BYV72F series









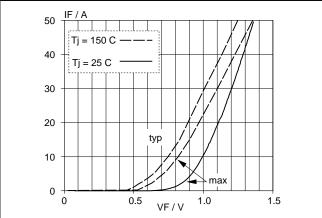
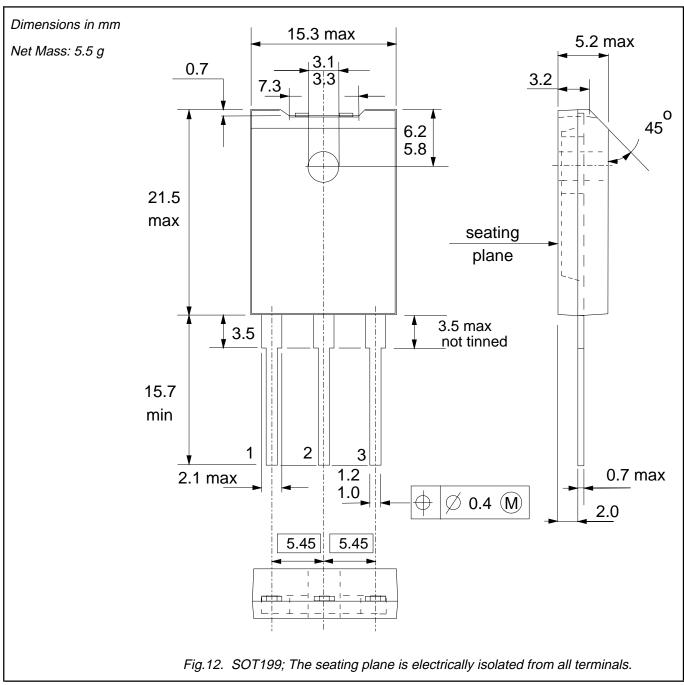


Fig.9. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_j

BYV72F series

MECHANICAL DATA



- Refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

BYV72F series

DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				
Product specification	This data sheet contains final product specifications.				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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